

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number	09/256643
Filing Date	February 23, 1999
First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 1 of 2

Attorney Docket No: 00303.324US2

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
MT	US-3,792,465	02/12/1974	Collins, D. R., et al	340	324 R	12/30/1971
	US-5,393,999	02/28/1995	Malhi, S.	257	289	06/09/1994
	US-5,557,122	09/17/1996	Shrivastava, R., et al	257	309	05/12/1995
	US-5,661,312	08/26/1997	Weitzel, C. E., et al	257	77	03/30/1995
	US-5,698,869	12/16/1997	Yoshimi, M., et al	257	192	09/13/1995
	US-5,734,181	03/31/1998	Ohba, R., et al	257	77	05/20/2002
	US-5,798,548	08/25/1998	Fujiwara, H.	257	319	05/17/1996
	US-5,808,336	09/15/1998	Miyawaki, M.	257	315	05/05/1995
	US-5,886,376	03/23/1999	Acovic, A., et al	257	316	07/01/1996
	US-5,926,740	07/20/1999	Forbes, L., et al	438	763	10/27/1997
	US-5,976,926	11/02/1999	Wu, J. Z., et al	438	237	10/10/1997
	US-5,989,958	11/23/1999	Forbes, L.	438	257	08/20/1998
	US-6,031,263	02/29/2000	Forbes, L. et al	257	315	07/29/1997
	US-6,084,248	07/04/2000	Inoue, S.	257	66	02/03/1998
	US-6,093,937	07/25/2000	Yamazaki, S. et al	257	59	02/19/1997
	US-6,099,574	08/08/2000	Fukuda, S., et al	703	14	12/16/1997
	US-6,130,147	10/10/2000	Major, J.S., et al	438	604	03/18/1997
	US-6,271,566	08/07/2001	Tsuchiaki, M.	257	347	11/16/1999
MT	US-6,297,521	10/02/2001	Forbes, L., et al	257	76	08/14/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
MT	JP-2203564	08/13/1990	Fujii, Y., et al	HO1 L	29/46	
MT	JP-57-126175	08/05/1982	Hamakawa, Y., et al	H01L	31/04	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

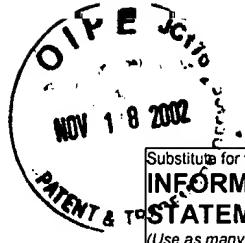
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MT		BELTRAM, F., et al. , "GaAIAs/GaAs Floating-Gate Memory Devices with Graded-Gap Injector Grown by Molecular-Beam Epitaxy", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-7, (Dec. 1988), 2451	
		BELTRAM, F., et al. , "Memory phenomena in heterojunction structures: Evidence for suppressed thermionic emission", <u>Appl. Phys. Lett.</u> , 53(5), (1988), pp. 376-378	
		BURNS, S.G. , et al. , <u>In: Principles of Electronic Circuits</u> , West Publishing Company, St. Paul, MN, (1987), 382-383	
MT		BURNS, S., et al. , <u>In: Principles of Electronic Circuits</u> , West Publishing Company, (1987), pg. 380	

EXAMINER

Michael Trinh

DATE CONSIDERED

1/24/02



431 2/2

PTO/SB/08A(10-01)
Approved for use through 10/31/2002. OMB 051-0031
US Patent & Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	09/256643
	Filing Date	February 23, 1999
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2822
	Examiner Name	Trinh, Michael
Sheet 2 of 2		Attorney Docket No: 00303.324US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
mt		CAPASSO, F., et al. , "New Floating-Gate AlGaAs/GaAs Memory Devices with Graded-Gap Electron Injector and Long Retention Times", <u>IEEE Electron Device Letters</u> , (1988), pp. 377-379	
		LOTT, J., et al. , "Anisotropic thermionic emission of electrons contained in GaAs/AlAs floating gate device structures", <u>Appl. Phys. Lett.</u> , 55(12), (1989), pp. 1226-1228	
		LOTT, J.A. , et al. , "Charge Storage in InAlAs/InGaAs/InP Floating Gate Heterostructures", <u>Electronics Letters</u> , 26, (July 5, 1990), 972-973	
		MOHAMMAD, S..N. , et al. , "Emerging Gallium Nitride Based Devices", <u>Proceedings of the IEEE</u> , 83, (Oct. 1995), 1306-1355	
		NEUDECK, P., et al. , "Electrical Characterization of a JFET-Accessed GaAs Dynamic RAM Cell", <u>IEEE Electron Device Letters</u> , 10(11), (1989), pp. 477-480	
		NG, K., In: <u>Complete Guide To Semiconductor Devices</u> , McGraw-Hill, Inc. New York, (1995), pp. 322-328, 605-608	
		QIAN, Q., et al. , "Multi-Day Dynamic Storage of Holes at the AlAs/GaAs Interface", <u>IEEE Electron Device Letters</u> , EDL-7(11), (1986), pp. 607-609	
		SHARMA, B., et al. , "Heterojunction Devices", In: <u>Semiconductor Heterojunctions</u> , Pergamon Press, New York, (1974), pp. 133-137	
		STREETMAN, B., In: <u>Solid State Electronic Devices</u> , 4th Edition, Prentice Hall, New Jersey, (1995), pp. 217-219, 392-394	
		SZE, S.M. , In: <u>Physics of Semiconductor Devices</u> , 2nd Edition, John Wiley & Sons, New York, (1981), pp. 122-129, 700-703, 708-710, 763-765	
mt		WOLF, S., "Semiconductor Memory Process Integration", <u>Silicon Processing for The VLSI Era</u> , Volume 2: Process Integration, (1990), pp. 623-628	

EXAMINER	Michael Trinh	DATE CONSIDERED	1/24/02
----------	---------------	-----------------	---------

Substitute Disclosure Statement Form (PTO-1449)
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached